REVISION HISTORY

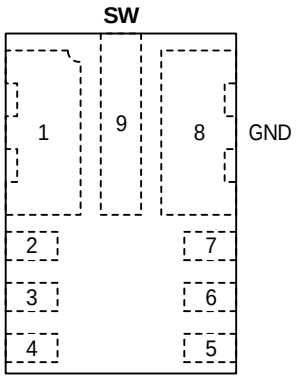
DEVICE ORDER INFORMATION

ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature unless otherwise noted(1)

DESCRIPTION	MIN	MAX	UNIT
BST	-0.3	48	V
VIN, SW, EN	-0.3	42	V
FB, COMP	-0.3	6	V

PIN CONFIGURATION

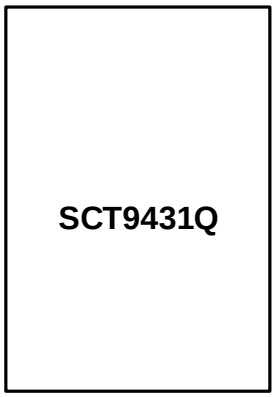


Top View: FCQFN2X3-9L

BST	6	Power supply for the high-side power MOSFET gate driver. Must connect a 0.1uF or greater ceramic capacitor between BST pin and SW node.

ELECTRICAL CHARACTERISTICS

APPLICATION INFORMATION



Design Parameters	Example Value
Input Voltage	12

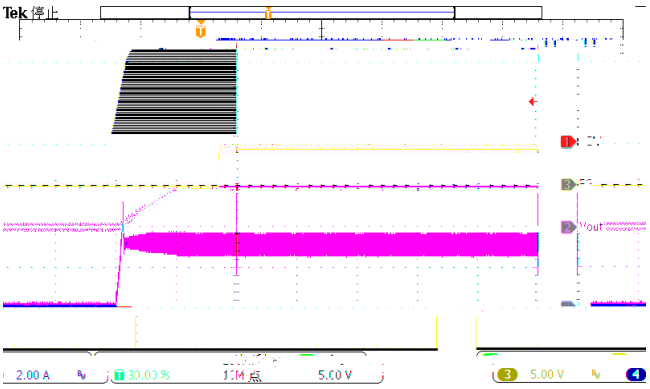
(3)

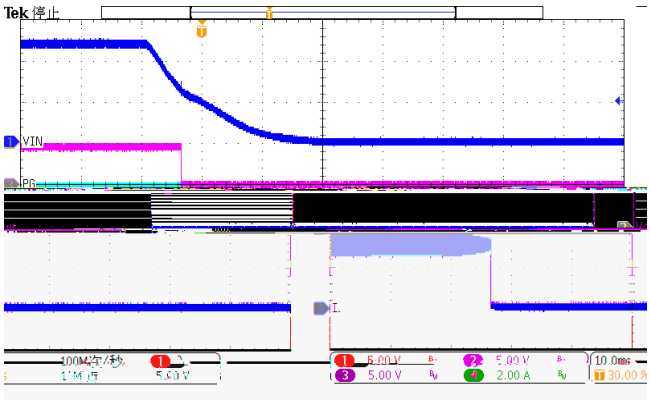
(4)

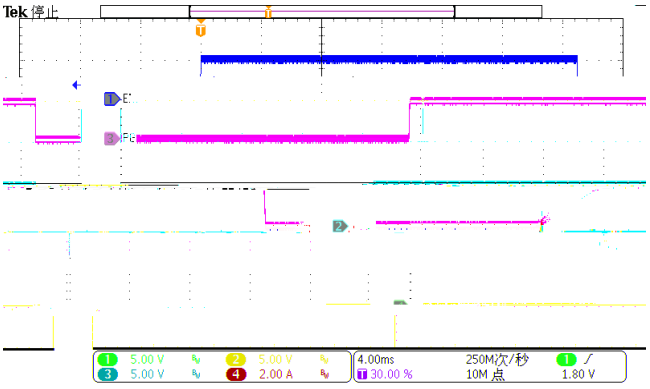
(5)

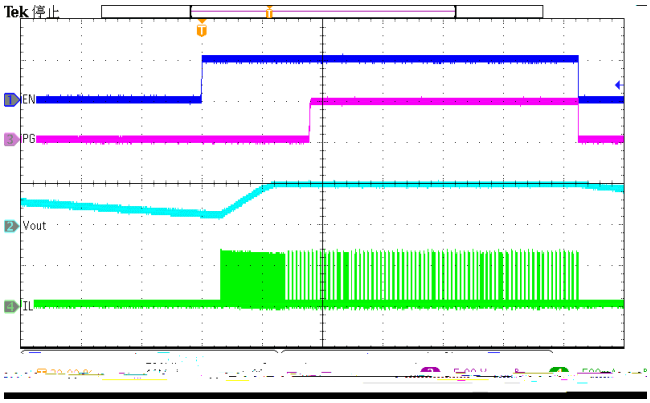
(10)

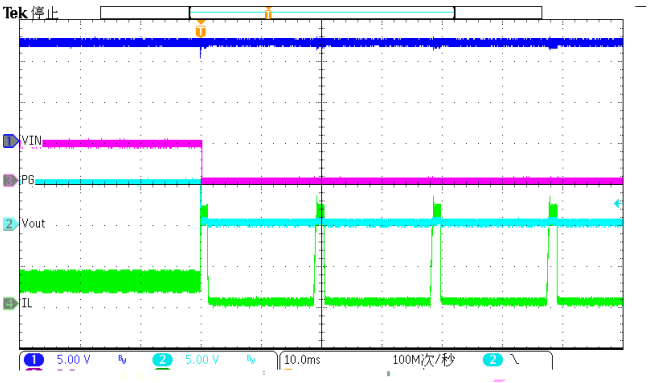
(11)

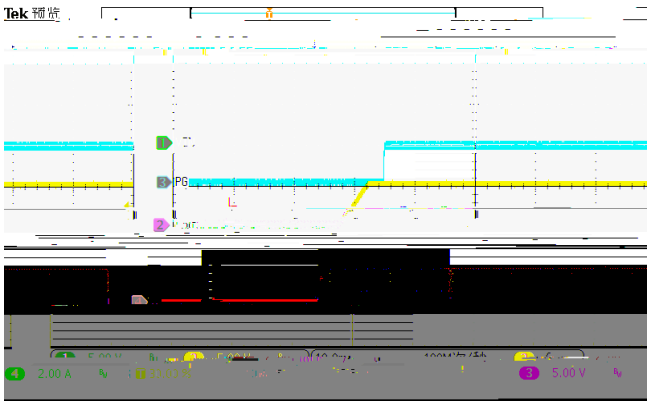

Tek 停止
Vout
2.00 A
30.00 %
1M 点
5.00 V
5.00 V

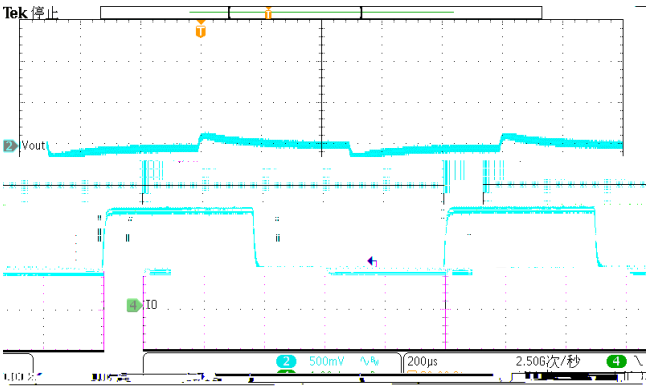

Tek 停止
VIN
PG
I
100M次/秒
1M 点
5.00 V
5.00 V
5.00 V
2.00 A
10.0ms
30.00 %

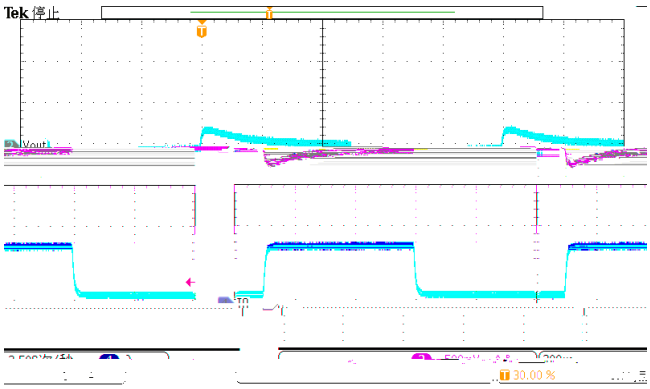

Tek 停止
5.00 V
5.00 V
5.00 V
2.00 A
4.00ms
30.00 %
250M次/秒
10M 点
1.80 V

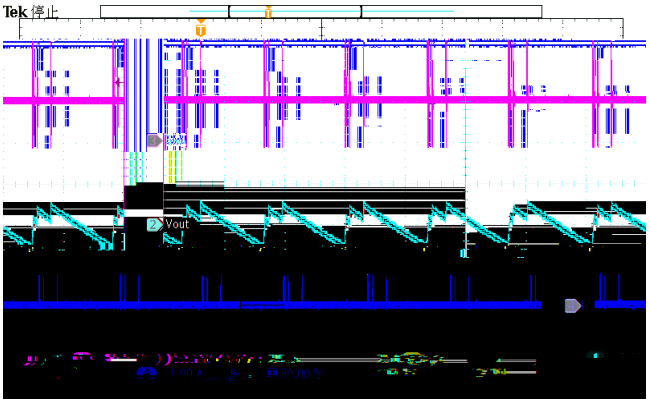

Tek 停止
EN
PG
Vout
IL

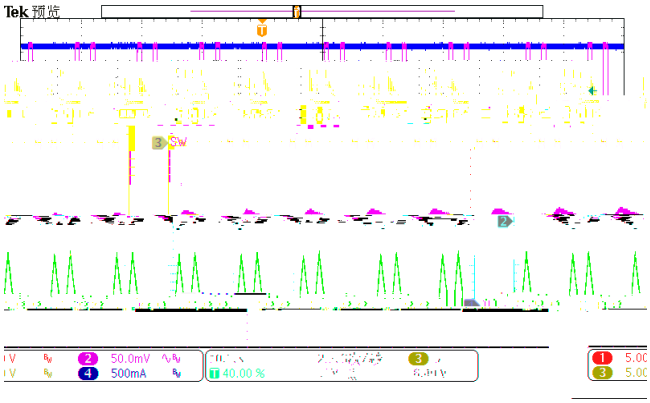

Tek 停止
VIN
PG
Vout
IL
5.00 V
5.00 V
10.0ms
100M次/秒

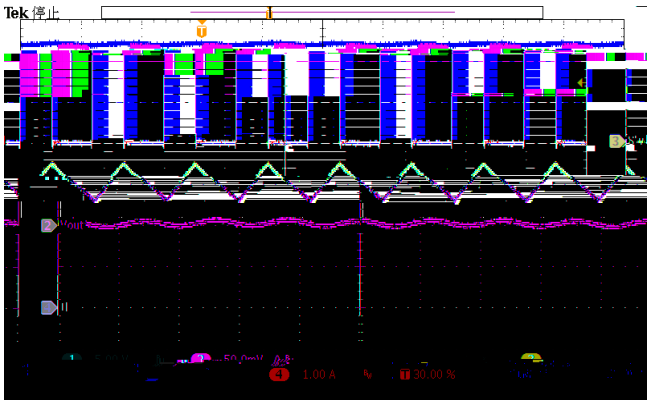

Tek 预览
PG
2.00 A
5.00 V

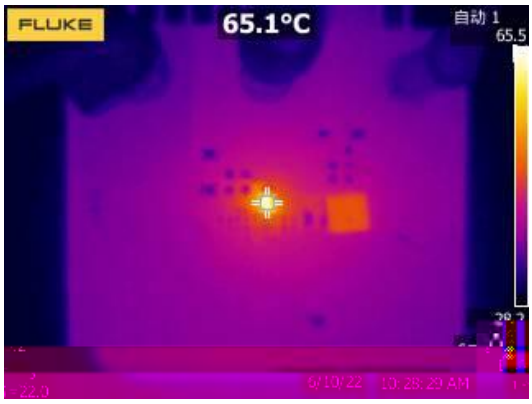

Tek 停止
Vout
IO
2 500mV
200µs
2.50G次/秒
4


Tek 停止
Vout
IO
30.00 %


Tek 停止
Vout


Tek 预览
SW
2 50.0mV
4 500mA
40.00 %

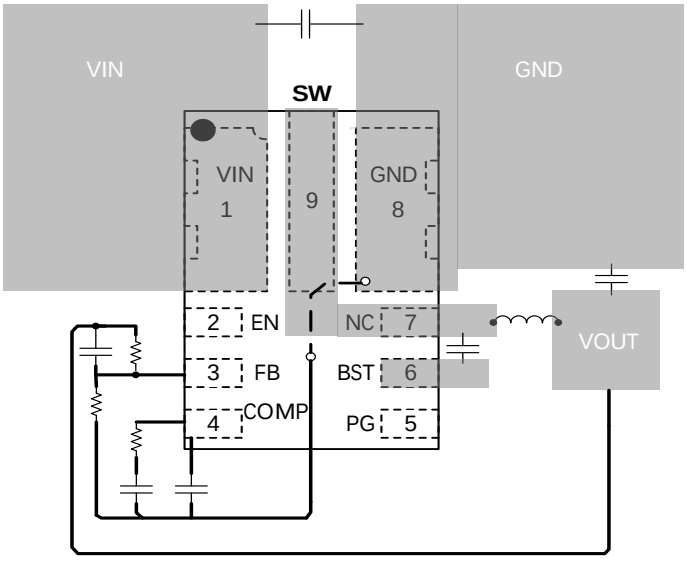

Tek 停止
Vout
4 1.00 A
30.00 %

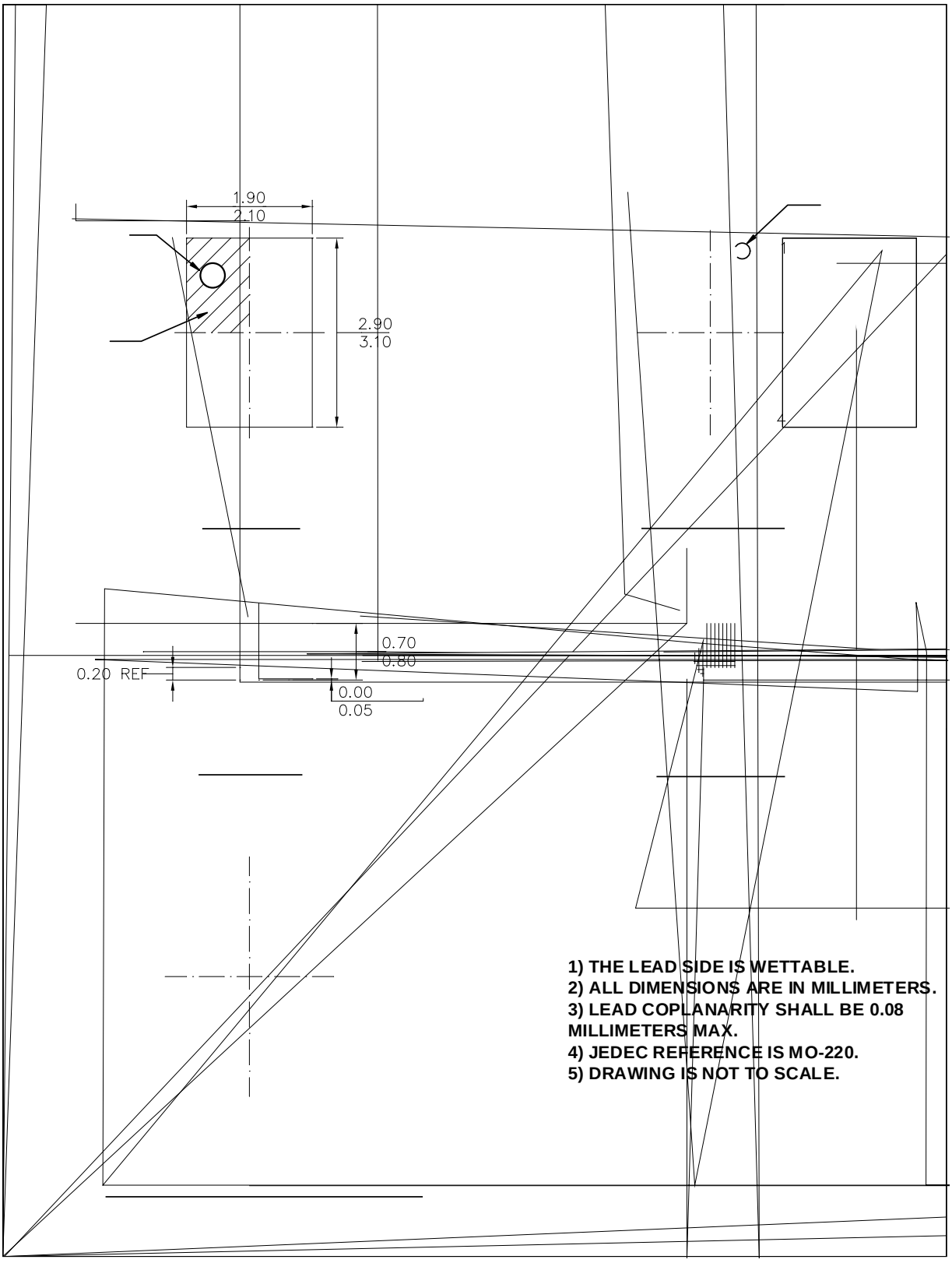

FLUKE
65.1°C
自动 1
65.5

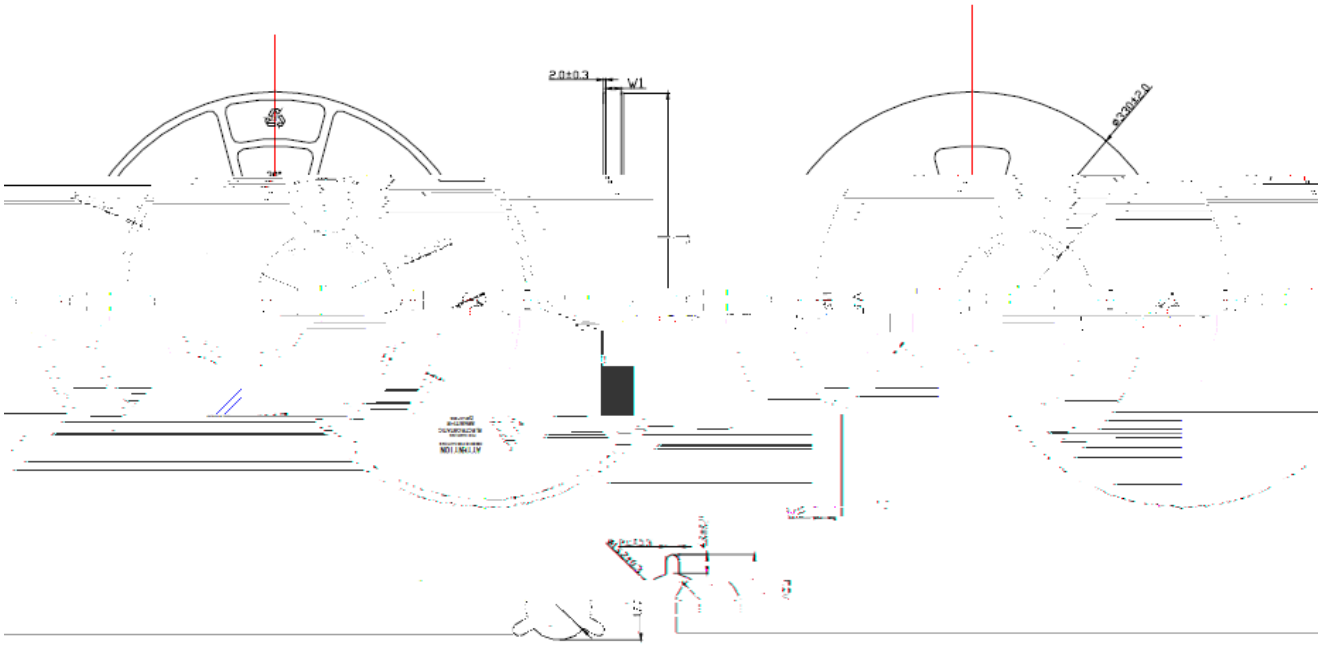
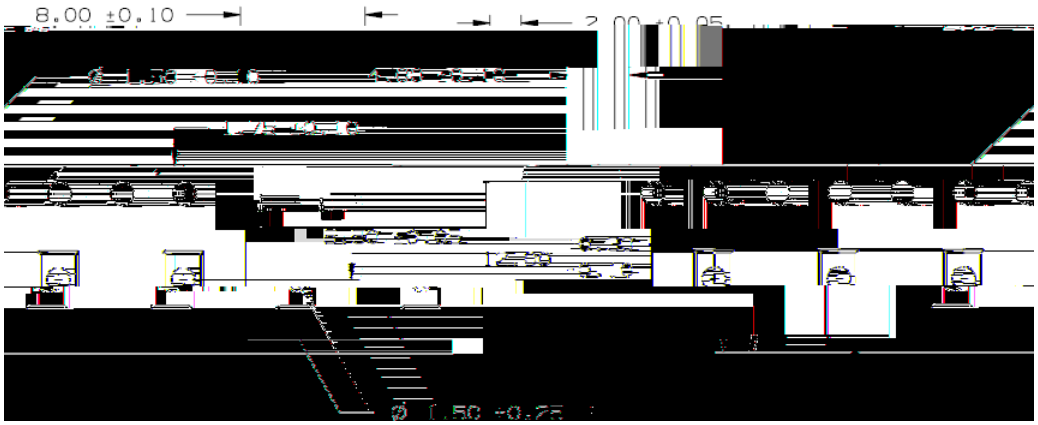
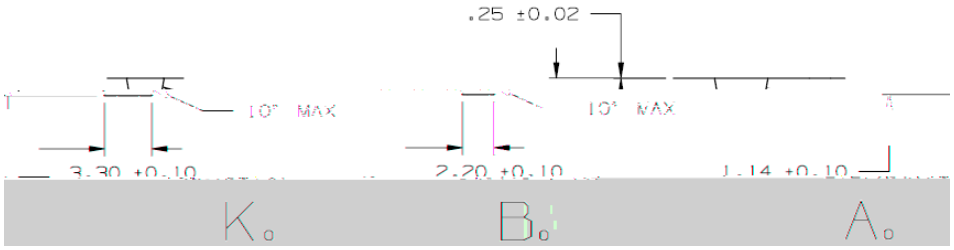
1.

2.
3.
4.
5.
6.
7.

8.





1) THE LEAD SIDE IS WETTABLE.
2) ALL DIMENSIONS ARE IN MILLIMETERS.
3) LEAD COPLANARITY SHALL BE 0.08 MILLIMETERS MAX.
4) JEDEC REFERENCE IS MO-220.
5) DRAWING IS NOT TO SCALE.

TAPE AND REEL INFORMATION